

### Supplementary information: S1

A comparative variation of Raman active modes at two different temperature conditions are listed in the table S1. The values exhibit a significant shift for  $\nu_2$ ,  $\nu_3$ ,  $\nu_5$  and  $\nu_6$  modes towards lower wave-number (or lower frequency) region, whereas  $\nu_1$  and  $\nu_4$  modes are shift towards higher wave-number (or higher frequency) direction. Due to the heat treatment the iodine vacancy was created and the vacancies are occupied by oxygen that forms stronger bismuth-oxygen (Bi-O) bond, which alters the  $\text{BiI}_6$  octahedra network, as a consequence the modes  $\nu_1$  and  $\nu_4$  are shifted. The presence of  $\text{O}^{2-}$  ion in the lattice makes a weaker the I-I interaction of the iodine molecule ( $\text{I}_2$ ) surrounding the tri-iodide ( $\text{I}_3^-$ ) and on the longer poly-iodide  $[\text{I} \dots \text{I}_3 \dots \text{I-I}]_n$  chains, as result the frequency shift was observed for  $\nu_2$ ,  $\nu_3$ ,  $\nu_5$  and  $\nu_6$  modes. Broadening effect is more prominent for  $\nu_5$  and  $\nu_6$  modes that can be related to the compositional disorder in presence of  $\text{O}^{2-}$  ion in the lattice.

**Table S1:** Raman active modes ( $\text{cm}^{-1}$ ) of  $\text{BiI}_3$  material, measured at 30 °C and 60 °C.

Modes	$\nu_1$	$\nu_2$	$\nu_3$	$\nu_4$	$\nu_5$	$\nu_6$
Raman shift ( $\text{cm}^{-1}$ ) @ 30 °C	65.0	93.5	123.2	145.5	245.6	315.2
Raman shift ( $\text{cm}^{-1}$ ) @ 60 °C	67.1	91.2	122.2	149.6	232.4	313.5

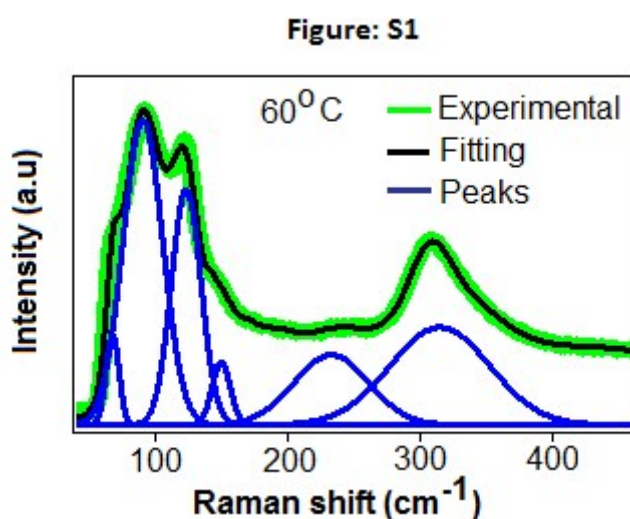


Figure S1: Deconvoluted Raman spectra @ 60 °C of bismuth iodide.

### Supplementary information: S2

The variation of capacitance value with respect to the applied bias that can be expressed by the following relations [ref]:

$$C^{-2} = \frac{2(V_d + V)}{(q\varepsilon\varepsilon_0 A^2 N_d)} \quad (1)$$

$$\frac{d(C^{-2})}{dV} = \frac{2}{(q\varepsilon\varepsilon_0 A^2 N_d)} \quad (2)$$

Where  $V_d$  is the diffusion potential extracted from the intercept of  $C^{-2}$  vs.  $V$  plot on the  $V$  axis,  $q$  is the electronic charge,  $\varepsilon$  is the dielectric constant of the material,  $\varepsilon_0$  is the dielectric constant of the vacuum,  $A$  is the contact area and  $N_d$  is the carrier concentration of the material.

### Supplementary information: S3

The complex electric modulus ( $M^*$ ) spectra were extracted from the complex dielectric constant ( $\varepsilon^*$ ) by using the following relations:

$$M^* = \frac{1}{(\varepsilon^*)} = M' + jM'' \quad (4)$$

$$M' = \left( \frac{\varepsilon'}{\varepsilon'^2 + \varepsilon''^2} \right), \quad M'' = \left( \frac{\varepsilon''}{\varepsilon'^2 + \varepsilon''^2} \right) \quad (5)$$

Where,  $M'$  and  $M''$  are the real and imaginary part of electric modulus and  $\varepsilon'$  and  $\varepsilon''$  are the real and imaginary part of dielectric constant respectively.